### **Description**

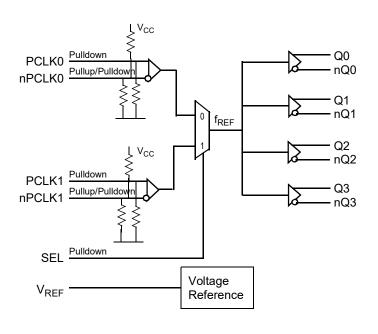
The 8SLVP1204 is a high-performance differential LVPECL fanout buffer. The device is designed for the fanout of high-frequency, very low additive phase-noise clock and data signals. The 8SLVP1204 is characterized to operate from a 3.3V or 2.5V power supply.

Guaranteed output-to-output and part-to-part skew characteristics make the 8SLVP1204 ideal for clock distribution applications that demand well-defined performance and repeatability. Two selectable differential inputs and four low skew outputs are available. The integrated bias voltage reference enables easy interfacing of single-ended signals to the device inputs. The device is optimized for low power consumption and low additive phase noise.

#### **Features**

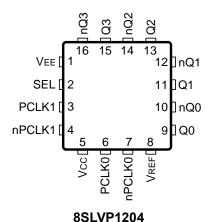
- Four low skew, low additive jitter LVPECL output pairs
- Two selectable, differential clock input pairs
- Differential PCLKx pairs can accept the following differential input levels: LVDS, LVPECL, CML
- Differential PCLKx pairs can also accept single-ended LVCMOS levels. See Applications Information, "Wiring the Differential Input to Accept Single-Ended Levels" (Figures 1A and 1B)
- · Maximum input clock frequency: 2GHz
- LVCMOS interface levels for the control input, (input select)
- Output skew: 5ps (typical), at 3.63V
- Propagation delay: 200ps (typical), at 3.63V
- Low additive phase jitter, RMS; f<sub>REF</sub> = 156.25MHz, V<sub>PP</sub> = 1V, 12kHz - 20MHz: 40fs (maximum), at 3.63V
- Maximum device current consumption (I<sub>EE</sub>): 60mA (maximum), at 3.63V
- Full 3.3V±5%, 3.3V±10% or 2.5V±5% supply
- Lead-free (RoHS 6), 16-Lead VFQFPN packaging
- -40°C to 85°C ambient operating temperature
- Supports case temperature ≤ 105°C operations
- Supports PCI Express Gen1-5

### **Block Diagram**



### Pin Assignment

1



16-Lead, 3mm x 3mm VFQFPN Package



# **Pin Descriptions and Characteristics**

**Table 1. Pin Descriptions** 

Number	Name	Ту	ре	Description
1	V <sub>EE</sub>	Power		Negative supply pin.
2	SEL	Input	Pulldown	Reference select control pin. See Table 3 for function. LVCMOS/LVTTL interface levels.
3	PCLK1	Input	Pulldown	Non-inverting differential LVPECL clock/data input.
4	nPCLK1	Input	Pullup/ Pulldown	Inverting differential LVPECL clock/data input. V <sub>CC</sub> /2 default when left floating.
5	V <sub>CC</sub>	Power		Power supply pins.
6	PCLK0	Input	Pulldown	Non-inverting differential LVPECL clock/data input.
7	nPCLK0	Input	Pullup/ Pulldown	Inverting differential LVPECL clock/data input. V <sub>CC</sub> /2 default when left floating.
8	V <sub>REF</sub>	Output		Bias voltage reference for the PCLK inputs.
9, 10	Q0, nQ0	Output		Differential output pair 0. LVPECL interface levels.
11, 12	Q1, nQ1	Output		Differential output pair 1. LVPECL interface levels.
13, 14	Q2, nQ2	Output		Differential output pair 2. LVPECL interface levels.
15, 16	Q3, nQ3	Output		Differential output pair 3. LVPECL interface levels.

NOTE: Pulldown and Pullup refers to an internal input resistors. See Table 2, Pin Characteristics, for typical values.

**Table 2. Pin Characteristics** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance			2		pF
R <sub>PULLDOWN</sub>	Input Pulldown Resistor			51		kΩ
R <sub>PULLUP</sub>	Input Pullup Resistor			51		kΩ

### **Function Table**

**Table 3. SEL Input Selection Function Table** 

Input	
SEL	Operation
0 (default)	PCLK0, nPCLK0 is the selected differential clock input.
1	PCLK1, nPCLK1 is the selected differential clock input.

NOTE: SEL is an asynchronous control.



### **Absolute Maximum Ratings**

Exposure to absolute maximum rating conditions for extended periods may affect product reliability. Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of the product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied.

Item	Rating
Supply Voltage, V <sub>CC</sub>	4.6V
Inputs, V <sub>I</sub>	-0.5V to V <sub>CC</sub> + 0.5V
Outputs, I <sub>O</sub> (LVPECL)	
Continuous Current	50mA
Surge Current	100mA
Input Sink/Source, I <sub>REF</sub>	±2mA
Maximum Junction Temperature, T <sub>J,MAX</sub>	150°C
Storage Temperature, T <sub>STG</sub>	-65°C to 150°C
ESD - Human Body Model, NOTE 1	2000V
ESD - Charged Device Model, NOTE 1	1500V

NOTE 1: According to JEDEC/JESD 22-A114/22-C101.

### **Recommended Operating Conditions**

Symbol	Parameter	Minimum	Typical	Maximum	Units
T <sub>A</sub>	Ambient air temperature	-40		85	°C
T <sub>J</sub>	Junction temperature			125	°C

NOTE 1: It is the user's responsibility to ensure that device junction temperature remains below the maximum allowed.

NOTE 2: All conditions in the table must be met to guarantee device functionality.

NOTE 3: The device is verified to the maximum operating junction temperature through simulation.

#### **DC Electrical Characteristics**

Table 4A. Power Supply DC Characteristics,  $V_{CC}$  = 3.3V ±10%,  $V_{EE}$  = 0V,  $T_A$  = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>CC</sub>	Power Supply Voltage		2.97	3.3V	3.63	V
I <sub>EE</sub>	Power Supply Current			53	60	mA
I <sub>CC</sub>	Power Supply Current	Q0 to Q3 terminated $50\Omega$ to $V_{CC}$ – $2V$		170	204	mA

Table 4B. Power Supply DC Characteristics,  $V_{CC} = 3.3V \pm 5\%$ ,  $V_{EE} = 0V$ ,  $T_A = -40$ °C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>CC</sub>	Power Supply Voltage		3.135	3.3V	3.465	V
I <sub>EE</sub>	Power Supply Current			53	60	mA
I <sub>CC</sub>	Power Supply Current	Q0 to Q3 terminated $50\Omega$ to $V_{CC}$ – $2V$		170	204	mA



### Table 4C. Power Supply DC Characteristics, $V_{CC}$ = 2.5V ±5%, $V_{EE}$ = 0V, $T_A$ = -40°C to 85°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V <sub>CC</sub>	Power Supply Voltage		2.375	2.5V	2.625	V
I <sub>EE</sub>	Power Supply Current			49	55	mA
I <sub>CC</sub>	Power Supply Current	Q0 to Q3 terminated $50\Omega$ to $V_{CC}$ – $2V$		170	199	mA

# Table 4D. LVCMOS/LVTTL DC Characteristics, $V_{CC}$ = 3.3V ±10%, $V_{EE}$ = 0V, $T_A$ = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V	V <sub>IH</sub> Input High Voltage		V <sub>CC</sub> = 3.63V	2.2		V <sub>CC</sub> + 0.3	V
V IH			V <sub>CC</sub> = 2.625V	1.7		V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	Input Low Voltage		V <sub>CC</sub> = 3.63V	-0.3		0.8	V
VIL	Input Low Voltage		V <sub>CC</sub> = 2.625V	-0.3		0.7	V
I <sub>IH</sub>	Input High Current	SEL	V <sub>CC</sub> = V <sub>IN</sub> = 3.465V or 2.625V			150	μA
I <sub>IL</sub>	Input Low Current	SEL	V <sub>CC</sub> = 3.465V or 2.625V, V <sub>IN</sub> = 0V	-10			μA

# $\textbf{Table 4E. LVCMOS/LVTTL DC Characteristics, } V_{CC} = 3.3 \text{V} \pm 5\% \text{ or } 2.5 \text{V} \pm 5\%, V_{EE} = 0 \text{V}, T_{A} = -40 ^{\circ}\text{C to } 85 ^{\circ}\text{C}$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V	In most Hinda Walter ma		V <sub>CC</sub> = 3.465V	2.2		V <sub>CC</sub> + 0.3	V
$V_{IH}$	Input High Voltage		V <sub>CC</sub> = 2.625V	1.7		V <sub>CC</sub> + 0.3	V
V	Input Low Voltage		V <sub>CC</sub> = 3.465V	-0.3		0.8	V
$V_{IL}$	Input Low Voltage		V <sub>CC</sub> = 2.625V	-0.3		0.7	V
I <sub>IH</sub>	Input High Current	SEL	V <sub>CC</sub> = V <sub>IN</sub> = 3.465V or 2.625V			150	μΑ
I <sub>IL</sub>	Input Low Current	SEL	V <sub>CC</sub> = 3.465V or 2.625V, V <sub>IN</sub> = 0V	-10			μΑ



Table 4F. LVPECL DC Characteristics,  $V_{CC}$  = 3.3V ±10%,  $V_{EE}$  = 0V,  $T_A$  = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
I <sub>IH</sub>	Input High Current	PCLK0, nPCLK0 PCLK1, nPCLK1	$V_{CC} = V_{IN} = 3.63V$			150	μΑ
	Input Low Current	PCLK0, PCLK1	V <sub>CC</sub> = 3.63V, V <sub>IN</sub> = 0V	-10			μΑ
l IIL	Input Low Current	nPCLK0, nPCLK1	V <sub>CC</sub> = 3.63V, V <sub>IN</sub> = 0V	-150			μΑ
V <sub>REF</sub>	Reference Voltage f	or Input Bias	I <sub>REF</sub> = ±1mA	V <sub>CC</sub> – 1.6	V <sub>CC</sub> – 1.3	V <sub>CC</sub> – 1.1	V
V <sub>OH</sub>	Output High Voltage <sup>1</sup>			V <sub>CC</sub> – 1.1	V <sub>CC</sub> - 0.9	V <sub>CC</sub> - 0.7	V
V <sub>OL</sub>	Output Low Voltage <sup>1</sup>			V <sub>CC</sub> – 2.0	V <sub>CC</sub> – 1.65	V <sub>CC</sub> – 1.5	V

NOTE 1. Outputs terminated with  $50\Omega$  to  $\mbox{V}_{\mbox{CC}}$  – 2V.

Table 4G. LVPECL DC Characteristics,  $V_{CC}$  = 3.3V ±5%,  $V_{EE}$  = 0V,  $T_A$  = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
I <sub>IH</sub>	Input High Current	PCLK0, nPCLK0 PCLK1, nPCLK1	V <sub>CC</sub> = V <sub>IN</sub> = 3.465V			150	μΑ
	Input Low Current	PCLK0, PCLK1	V <sub>CC</sub> = 3.465V, V <sub>IN</sub> = 0V	-10			μA
l IIL	Input Low Current	nPCLK0, nPCLK1	V <sub>CC</sub> = 3.465V, V <sub>IN</sub> = 0V	-150			μΑ
$V_{REF}$	Reference Voltage f	for Input Bias	I <sub>REF</sub> = ±1mA	V <sub>CC</sub> – 1.6	V <sub>CC</sub> – 1.3	V <sub>CC</sub> – 1.1	V
V <sub>OH</sub>	Output High Voltage <sup>1</sup>			V <sub>CC</sub> – 1.1	V <sub>CC</sub> - 0.9	V <sub>CC</sub> - 0.7	V
V <sub>OL</sub>	Output Low Voltage	1		V <sub>CC</sub> - 2.0	V <sub>CC</sub> – 1.65	V <sub>CC</sub> – 1.5	V

NOTE 1. Outputs terminated with  $50\Omega$  to  $\mbox{V}_{\mbox{CC}}$  – 2V.

Table 4H. LVPECL DC Characteristics,  $V_{CC}$  = 2.5V ±5%,  $V_{EE}$  = 0V,  $T_A$  = -40°C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
I <sub>IH</sub>	Input High Current	PCLK0, nPCLK0 PCLK1, nPCLK1	V <sub>CC</sub> = V <sub>IN</sub> = 2.625V			150	μΑ
	Input Low Current	PCLK0, PCLK1	V <sub>CC</sub> = 2.625V, V <sub>IN</sub> = 0V	-10			μΑ
I <sub>IL</sub> Input Low Current	nPCLK0, nPCLK1	V <sub>CC</sub> = 2.625V, V <sub>IN</sub> = 0V	-150			μΑ	
V <sub>REF</sub>	Reference Voltage for Input Bias		I <sub>REF</sub> = ±1mA	V <sub>CC</sub> – 1.6	V <sub>CC</sub> – 1.3	V <sub>CC</sub> – 1.1	V
V <sub>OH</sub>	Output High Voltage <sup>1</sup>			V <sub>CC</sub> – 1.1	V <sub>CC</sub> - 0.9	V <sub>CC</sub> - 0.7	V
V <sub>OL</sub>	Output Low Voltage <sup>1</sup>			V <sub>CC</sub> - 2.0	V <sub>CC</sub> – 1.6	V <sub>CC</sub> – 1.5	V

NOTE 1. Outputs terminated with  $50\Omega$  to  $\mbox{V}_{\mbox{CC}}$  – 2V.



### **AC Electrical Characteristics**

Table 5A. AC Electrical Characteristics,  $V_{CC}$  = 3.3V ± 5% or 2.5V ±5%,  $V_{EE}$  = 0V,  $T_A$  = -40°C to 85°C<sup>1</sup>

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f <sub>REF</sub>		CLK[0:1], PCLK[0:1]				2	GHz
ΔV/Δt		CLK[0:1], PCLK[0:1]		1.5			V/ns
t <sub>PD</sub>	Propagation De	elay <sup>2</sup>	PCKx, nPCLKx to any Qx, nQx for V <sub>PP</sub> = 0.1V or 0.3V	120	200	320	ps
tsk(o)	Output Skew <sup>3 4</sup>				5	25	ps
tsk(i)	Input Skew <sup>4</sup>				5	50	ps
tsk(p)	Pulse Skew		f <sub>REF</sub> = 100MHz		5	20	ps
tsk(pp)	Part-to-Part Ske	ew <sup>4 5</sup>			100	200	ps
			f <sub>REF</sub> = 122.88MHz Sine Wave, V <sub>PP</sub> = 1V, Integration Range: 1kHz – 40MHz		170		fs
			f <sub>REF</sub> = 122.88MHz Sine Wave, V <sub>PP</sub> = 1V, Integration Range: 10kHz – 20MHz		114		fs
			f <sub>REF</sub> = 122.88MHz Sine Wave, V <sub>PP</sub> = 1V, Integration Range: 12kHz – 20MHz		114		fs
	Buffer Additive Phase Jitter, RMS; refer to Additive Phase Jitter Section		f <sub>REF</sub> = 156.25MHz Square Wave, V <sub>PP</sub> = 1V, Integration Range: 1kHz – 40MHz		42	51	fs
$t_{\sf JIT}$			f <sub>REF</sub> = 156.25MHz Square Wave, V <sub>PP</sub> = 1V, Integration Range: 10kHz – 20MHz		32	40	fs
			f <sub>REF</sub> = 156.25MHz Square Wave, V <sub>PP</sub> = 1V, Integration Range: 12kHz – 20MHz		32	40	fs
			f <sub>REF</sub> = 156.25MHz Square Wave, V <sub>PP</sub> = 0.5V, Integration Range: 1kHz – 40MHz		51	71	fs
			f <sub>REF</sub> = 156.25MHz Square Wave, V <sub>PP</sub> = 0.5V, Integration Range: 10kHz – 20MHz		38	52	fs
			f <sub>REF</sub> = 156.25MHz Square Wave, V <sub>PP</sub> = 0.5V, Integration Range: 12kHz – 20MHz		38	52	fs
t <sub>R</sub> / t <sub>F</sub>	Output Rise/ Fa	all Time	20% to 80%	35	90	180	ps
MUX <sub>ISOLATION</sub>	Mux Isolation <sup>6</sup>		f <sub>REF</sub> = 100MHz		77		dB
V	Peak-to-Peak Ir	nput	f <sub>REF</sub> < 1.5 GHz	0.1		1.5	V
$V_{PP}$	Voltage <sup>7</sup>		f <sub>REF</sub> > 1.5 GHz	0.2		1.5	V
M	Common Mode	Input		1.0		V <sub>CC</sub> - 0.6	V
$V_{CMR}$	Voltage <sup>7 8 9</sup>		V <sub>PP</sub> = > 247mV	0.8		V <sub>CC</sub> - 0.6	V
V (pp)	Output Voltage	Swing,	$V_{CC}$ = 3.3V, $f_{REF} \le 2GHz$	0.45	0.75	1.0	V
V <sub>O</sub> (pp)	Peak-to-Peak	<b>.</b>	$V_{CC}$ = 2.5V, $f_{REF} \le 2GHz$	0.4	0.65	1.0	V
	Differential Out	put	$V_{CC}$ = 3.3V, $f_{REF} \le 2GHz$	0.9	1.5	2.0	V
$V_{DIFF\_OUT}$	Voltage Swing, Peak-to-Peak		V <sub>CC</sub> = 2.5V, f <sub>REF</sub> ≤ 2GHz	0.8	1.3	2.0	V



- NOTE 1. Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.
- NOTE 2. Measured from the differential input crossing point to the differential output crosspoint.
- NOTE 3. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the differential cross point.
- NOTE 4. This parameter is defined in accordance with JEDEC Standard 65.
- NOTE 5. Defined as skew between outputs on different devices operating at the same supply voltage, same frequency, same temperature and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross point.
- NOTE 6. Qx, nQx outputs measured differentially. See MUX Isolation diagram in the Parameter Measurement Information section.
- NOTE 7. For single-ended LVCMOS input applications, refer to the Applications section *Wiring the Differential Input Levels to Accept Single-ended Levels* (Figures 1 and 2).
- NOTE 8.  $V_{IL}$  should not be less than -0.3V.  $V_{IH}$  should not be higher than  $V_{CC}$ .
- NOTE 9. Common mode input voltage is defined as the crosspoint.

Table 5B. AC Electrical Characteristics,  $V_{CC} = 3.3V \pm 10\%$ ,  $V_{EE} = 0V$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C^1$ 

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
f <sub>REF</sub>	Input Frequency	PCLK[0:1], nPCLK[0:1]				2	GHz
ΔV/Δt	Input <sup>2</sup> Edge Rate	PCLK[0:1], nPCLK[0:1]		1.5			V/ns
t <sub>PD</sub>	Propagation	Delay <sup>3</sup>	PCKx, nPCLKx to any Qx, nQx for V <sub>PP</sub> = 0.1V or 0.3V	120	230	325	ps
tsk(o)	Output Skev	<b>v</b> <sup>4 5</sup>			6	30	ps
<i>t</i> sk(i)	Input Skew <sup>4</sup>				6	55	ps
tsk(p)	Pulse Skew		f <sub>REF</sub> = 100MHz		7	25	ps
tsk(pp)	Part-to-Part	Skew <sup>4 6</sup>				200	ps
t <sub>R</sub> / t <sub>F</sub>	Output Rise	/ Fall Time	20% to 80%	35		200	ps
MUX <sub>ISOLATION</sub>	Mux Isolatio	n <sup>7</sup>	f <sub>REF</sub> = 100MHz		77		dB
V	Peak-to-Peak Input		f <sub>REF</sub> < 1.5 GHz	0.1		1.5	V
$V_{PP}$	Voltage <sup>8</sup>		f <sub>REF</sub> > 1.5 GHz	0.2		1.5	V
V.	Common Mo	ode Input		1.0		V <sub>CC</sub> - 0.6	V
$V_{CMR}$	Common Mode Input Voltage <sup>7 9 10</sup>		V <sub>PP</sub> = > 247mV	0.8		V <sub>CC</sub> - 0.6	V
\/ (pp)	Output Voltage Swing,		$V_{CC}$ = 3.3V, $f_{REF} \le 2GHz$	0.45	0.75	1.0	V
V <sub>O</sub> (pp)	Peak-to-Pea	ak	$V_{CC}$ = 2.5V, $f_{REF} \le 2GHz$	0.4	0.65	1.0	V
	Differential Output		$V_{CC}$ = 3.3V, $f_{REF} \le 2GHz$	0.9	1.5	2.0	V
V <sub>DIFF_OUT</sub>	Voltage Swi Peak-to-Pea	•	$V_{CC}$ = 2.5V, $f_{REF} \le 2GHz$	0.8	1.3	2.0	V

- NOTE 1. Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.
- NOTE 2. Input Edge Rate is the slope of  $\Delta v/\Delta t$  at the crosspoint of the differential pair signals.  $\Delta t$  is measured with  $\Delta V = 300 \text{mV}$  on one of the single-ended input pair signals.
- NOTE 3. Measured from the differential input crossing point to the differential output crosspoint.
- NOTE 4. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the differential cross point.
- NOTE 5. This parameter is defined in accordance with JEDEC Standard 65



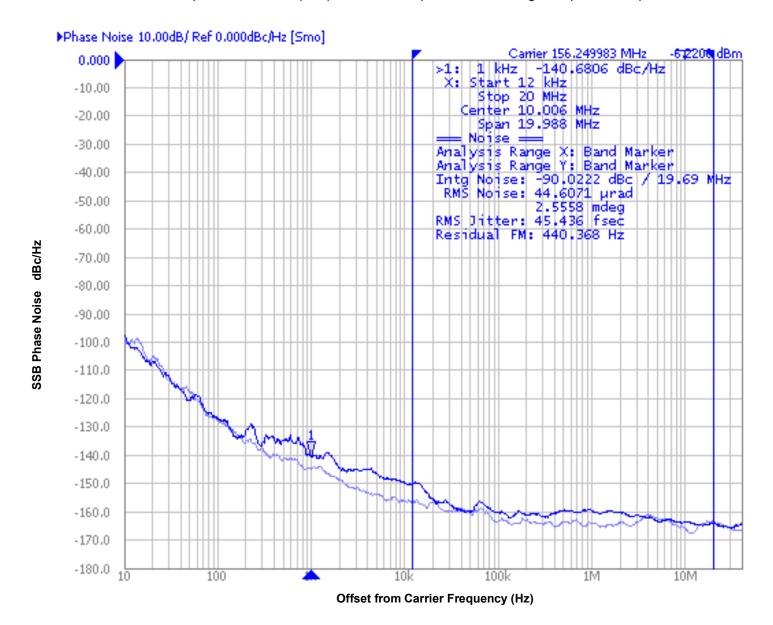
- NOTE 6. Defined as skew between outputs on different devices operating at the same supply voltage, same frequency, same temperature and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential crosspoint.
- NOTE 7. Qx, nQx outputs measured differentially. See MUX Isolation diagram in the Parameter Measurement Information section.
- NOTE 8. For single-ended LVCMOS input applications, refer to the Applications section *Wiring the Differential Input Levels to Accept Single-ended Levels* (Figures 1 and 2).
- NOTE 9.  $V_{IL}$  should not be less than -0.3V.  $V_{IH}$  should not be higher than  $V_{CC}$ .
- NOTE 10. Common mode input voltage is defined as the crosspoint.



#### **Additive Phase Jitter**

The spectral purity in a band at a specific offset from the fundamental compared to the power of the fundamental is called the *dBc Phase Noise*. This value is normally expressed using a Phase noise plot and is most often the specified plot in many applications. Phase noise is defined as the ratio of the noise power present in a 1Hz band at a specified offset from the fundamental frequency to the power value of the fundamental. This ratio is expressed in decibels (dBm) or a ratio

of the power in the 1Hz band to the power in the fundamental. When the required offset is specified, the phase noise is called a **dBc** value, which simply means dBm at a specified offset from the fundamental. By investigating jitter in the frequency domain, we get a better understanding of its effects on the desired application over the entire time record of the signal. It is mathematically possible to calculate an expected bit error rate given a phase noise plot.

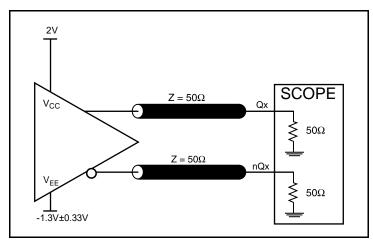


As with most timing specifications, phase noise measurements has issues relating to the limitations of the equipment. Often the noise floor of the equipment is higher than the noise floor of the device. This is illustrated above. The device meets the noise floor of what is shown, but can actually be lower. The phase noise is dependent on the input source and measurement equipment.

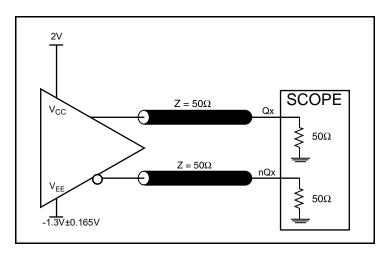
Measured using a Wenzel 156.25MHz Oscillator as the input source.



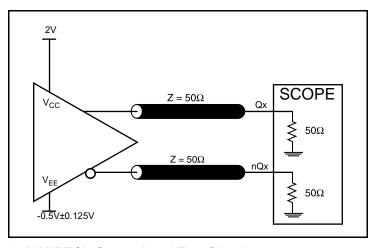
### **Parameter Measurement Information**



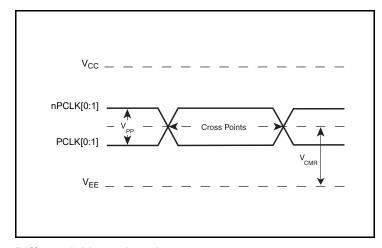
3.3V ±10% LVPECL Output Load Test Circuit



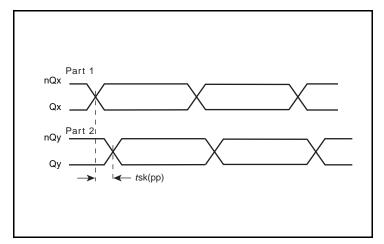
3.3V ±5% LVPECL Output Load Test Circuit



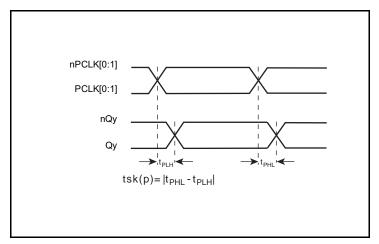
2.5V LVPECL Output Load Test Circuit



**Differential Input Level** 

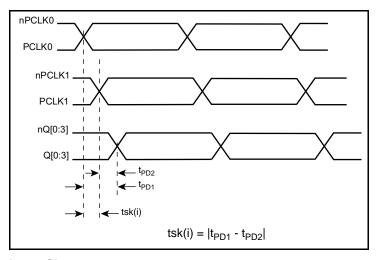


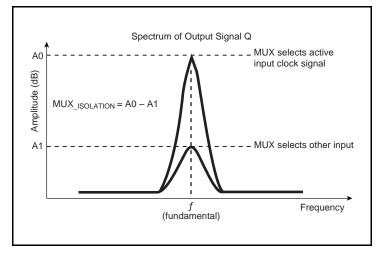
Part-to-Part Skew



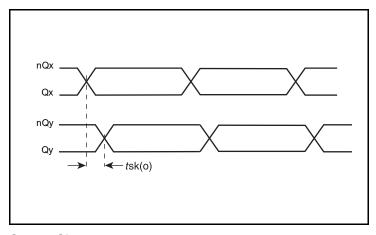
**Pulse Skew** 

# **Parameter Measurement Information, continued**

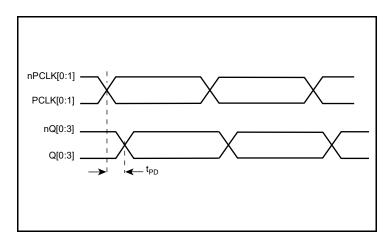




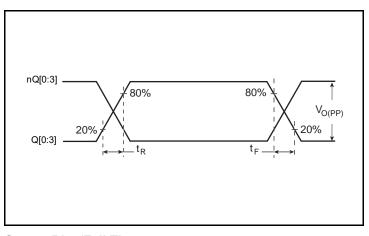
**Input Skew** 



**MUX** Isolation



**Output Skew** 



**Propagation Delay** 

**Output Rise/Fall Time** 



### **Applications Information**

#### Wiring the Differential Input to Accept Single-Ended Levels

The 8SLVP1204 inputs can be interfaced to LVPECL, LVDS, CML or LVCMOS drivers. *Figure 1A* illustrates how to DC couple a single LVCMOS input to the 8SLVP1204. The value of the series resistance RS is calculated as the difference between the transmission line impedance and the driver output impedance. This resistor should be placed close to the LVCMOS driver. To avoid cross-coupling of single-ended LVCMOS signals, apply the LVCMOS signals to no more than one PCLK input.

A practical method to implement Vth is shown in *Figure 1B* below. The reference voltage Vth = V1 =  $V_{CC}/2$ , is generated by the bias resistors R1 and R2. The bypass capacitor (C1) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible.

The ratio of R1 and R2 might need to be adjusted to position the V1 in the center of the input voltage swing. For example, if the input clock swing is 2.5V and  $V_{CC}$  = 3.3V, R1 and R2 value should be adjusted to set V1 at 1.25V. The values below apply when both the single-ended swing and  $V_{CC}$  are at the same voltage.

When using single-ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced, particularly if both input references are LVCMOS to minimize cross talk. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however  $V_{\rm IL}$  cannot be less than -0.3V and  $V_{\rm IH}$  cannot be more than  $V_{\rm CC}$  + 0.3V.

Figure 1B shows a way to attenuate the PCLK input level by a factor of two as well as matching the transmission line between the LVCMOS driver and the 8SLVP1204 at both the source and the load.

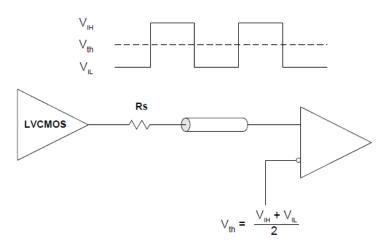


Figure 1A. DC-Coupling a Single LVCMOS Input to the 8SLVP1204

This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. R3 and R4 in parallel should equal the transmission line impedance; for most  $50\Omega$  applications, R3 and R4 will be  $100\Omega$ . The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver.

Though some of the recommended components of Figure 1B might not be used, the pads should be placed in the layout so that they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.

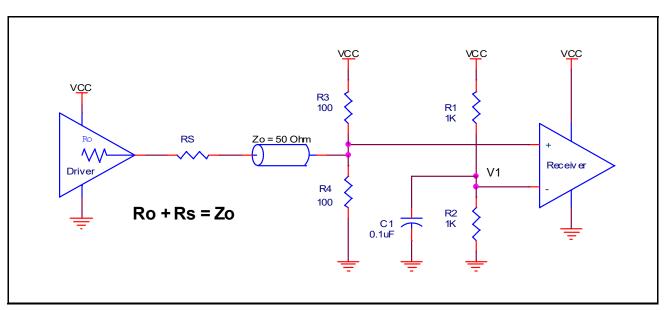


Figure 1B. Alternative DC Coupling a Single LVCMOS Input to the 8SLVP1204



#### 3.3V LVPECL Clock Input Interface

The PCLK /nPCLK accepts LVPECL, LVDS, CML and other differential signals. Both signals must meet the  $V_{PP}$  and  $V_{CMR}$  input requirements. Figures 2A to 2E show interface examples for the PCLK/ nPCLK input driven by the most common driver types. The

input interfaces suggested here are examples only. If the driver is from another vendor, use their termination recommendation. Please consult with the vendor of the driver component to confirm the driver termination requirements.

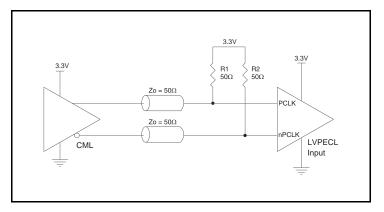


Figure 2A. PCLK/nPCLK Input Driven by a CML Driver

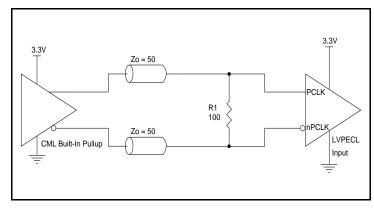


Figure 2B. PCLK/nPCLK Input Driven by a Built-In Pullup CML Driver

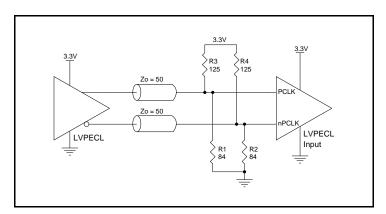


Figure 2C. PCLK/nPCLK Input Driven by a 3.3V LVPECL Driver

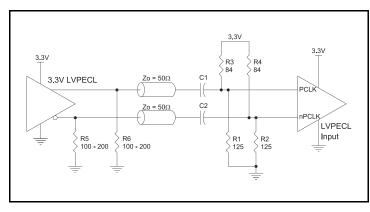


Figure 2D. PCLK/nPCLK Input Driven by a 3.3V LVPECL Driver with AC Couple

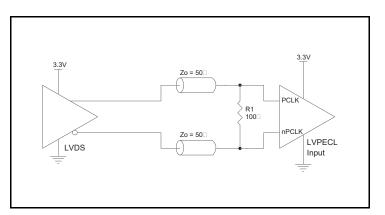


Figure 2E. PCLK/nPCLK Input Driven by a 3.3V LVDS Driver



#### 2.5V LVPECL Clock Input Interface

The PCLK /nPCLK accepts LVPECL, LVDS, CML and other differential signals. Both signals must meet the  $V_{PP}$  and  $V_{CMR}$  input requirements. *Figures 3A to 3E* show interface examples for the PCLK/ nPCLK input driven by the most common driver types. The

input interfaces suggested here are examples only. If the driver is from another vendor, use their termination recommendation. Please consult with the vendor of the driver component to confirm the driver termination requirements.

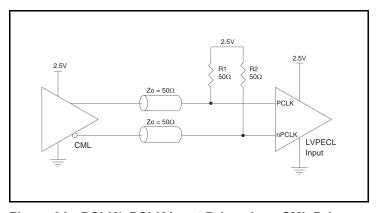


Figure 3A. PCLK/nPCLK Input Driven by a CML Driver

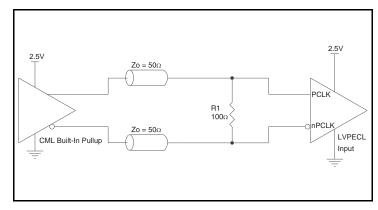


Figure 3B. PCLK/nPCLK Input Driven by a Built-In Pullup CML Driver

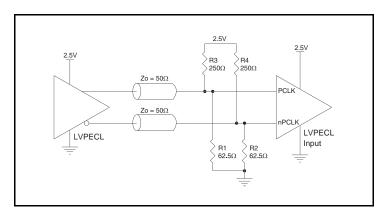


Figure 3C. PCLK/nPCLK Input Driven by a 2.5V LVPECL Driver

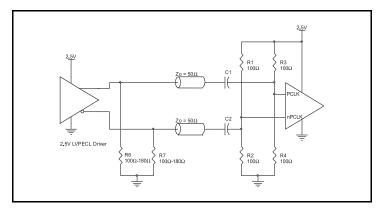


Figure 3D. PCLK/nPCLK Input Driven by a 2.5V LVPECL Driver with AC Couple

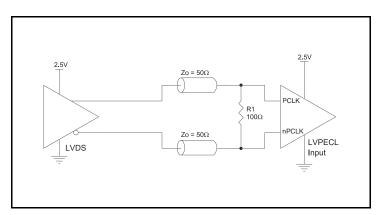


Figure 3E. PCLK/nPCLK Input Driven by a 2.5V LVDS Driver

#### **Recommendations for Unused Input and Output Pins**

#### Inputs:

#### **PCLK/nPCLK Inputs**

For applications not requiring the use of a differential input, both the PCLK and nPCLK pins can be left floating. Though not required, but for additional protection, a  $1 k\Omega$  resistor can be tied from PCLK to ground.

#### **Outputs:**

#### **LVPECL Outputs**

All unused LVPECL output pairs can be left floating. We recommend that there is no trace attached. Both sides of the differential output pair should either be left floating or terminated.

#### **VFQFPN EPAD Thermal Release Path**

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in *Figure 4*. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as "heat pipes". The number of vias (i.e. "heat pipes") are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor's Thermally/ Electrically Enhance Leadframe Base Package, Amkor Technology.

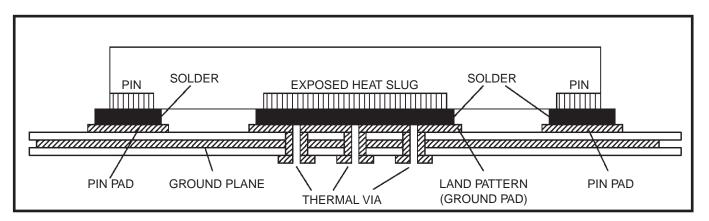


Figure 4. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)



### **Termination for 3.3V LVPECL Outputs**

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines.

The differential outputs are a low impedance follower output that generate ECL/LVPECL compatible outputs. Therefore, terminating resistors (DC current path to ground) or current sources must be used for functionality. These outputs are designed to drive  $50\Omega$ 

transmission lines. Matched impedance techniques should be used to maximize operating frequency and minimize signal distortion. *Figures 5A and 5B* show two different layouts which are recommended only as guidelines. Other suitable clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.

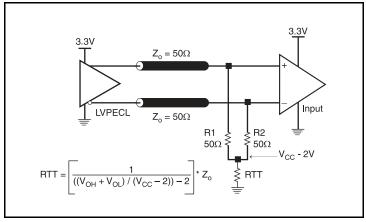


Figure 5A. 3.3V LVPECL Output Termination

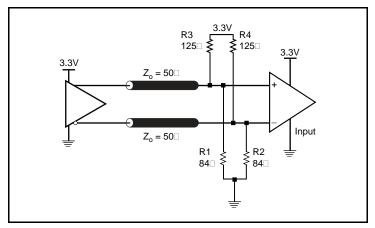


Figure 5B. 3.3V LVPECL Output Termination



### **Termination for 2.5V LVPECL Outputs**

Figure 6A and Figure 6B show examples of termination for 2.5V LVPECL driver. These terminations are equivalent to terminating  $50\Omega$  to  $V_{CC}$  – 2V. For  $V_{CC}$  = 2.5V, the  $V_{CC}$  – 2V is very close to ground

level. The R3 in Figure 6B can be eliminated and the termination is shown in *Figure 6C*.

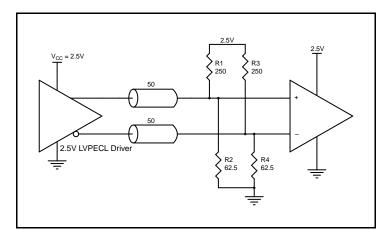


Figure 6A. 2.5V LVPECL Driver Termination Example

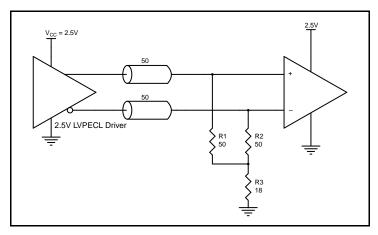


Figure 6B. 2.5V LVPECL Driver Termination Example

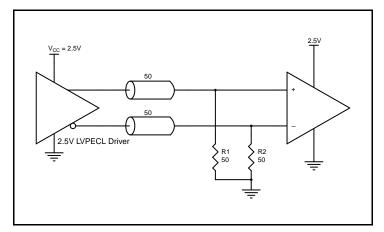


Figure 6C. 2.5V LVPECL Driver Termination Example



### Termination for Q, nQ LVPECL Outputs AC-Coupled into HCSL-Receiver

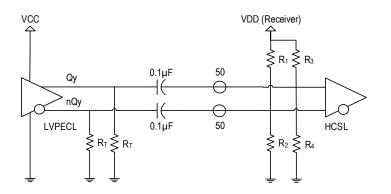


Figure 7. LVPECL Output AC-Coupled into HCSL Receiver

**Table 6. Termination Resistors** 

	V <sub>CC</sub> = 2.5V	V <sub>CC</sub> = 3.3V
R <sub>T</sub>	100Ω	180Ω

**Table 7. HCSL Receiver Voltage Bias** 

	V <sub>DD</sub> = 2.5V	V <sub>DD</sub> = 3.3V
R <sub>1</sub> , R <sub>3</sub>	357Ω	470Ω
R <sub>2</sub> , R <sub>4</sub>	58Ω	56Ω



#### 3.3V ±10% Power Considerations

This section provides information on power dissipation and junction temperature for the 8SLVP1204. Equations and example calculations are also provided.

#### 1. Power Dissipation.

The total power dissipation for the 8SLVP1204 is the sum of the core power plus the power dissipated due to loading. The following is the power dissipation for  $V_{CC} = 3.63V$ .

NOTE: Please refer to Section 3 for details on calculating power dissipated due to loading.

The maximum current at 85° is as follows:

 $I_{EE\ MAX} = 65mA$ 

- Power (core)<sub>MAX</sub> = V<sub>CC\_MAX</sub> \* I<sub>EE\_MAX</sub> = 3.63V \* 60mA = 217.80mW
- Power (outputs)<sub>MAX</sub> = 33.2mW/Loaded Output pair
   If all outputs are loaded, the total power is 4 \* 33.2mW = 132.8mW

Total Power\_MAX (3.63V, with all outputs switching) = 217.80mW + 132.8mW = 350.60mW

#### 2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: Tj =  $\theta_{JA}$  \* Pd\_total + T<sub>A</sub>

Tj = Junction Temperature

 $\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

Pd\_total = Total Device Power Dissipation (example calculation is in section 1 above)

T<sub>A</sub> = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 74.7°C/W per Table 6 below.

Therefore, Ti for an ambient temperature of 85°C with all outputs switching is:

 $85^{\circ}\text{C} + 0.351\text{W} * 74.7^{\circ}\text{C/W} = 111.2^{\circ}\text{C}$ . This is below the limit of  $125^{\circ}\text{C}$ .

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 8. Thermal Resistance  $\theta_{\text{JA}}$  for 16-Lead VFQFPN, Forced Convection

$\theta_{JA}$ by Velocity				
Meters per Second	0	1	2.5	
Multi-Layer PCB, JEDEC Standard Test Boards	74.7°C/W	65.3°C/W	58.5°C/W	



#### 3. Calculations and Equations.

The purpose of this section is to calculate the power dissipation for the LVPECL output pair.

LVPECL output driver circuit and termination are shown in Figure 7.

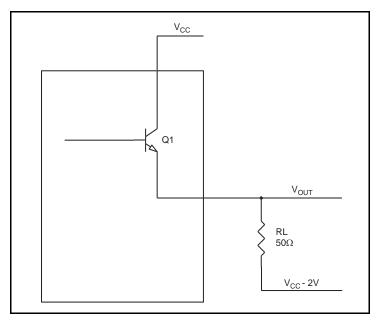


Figure 8. LVPECL Driver Circuit and Termination

To calculate power dissipation due to loading, use the following equations which assume a  $50\Omega$  load, and a termination voltage of  $V_{CC}$  – 2V. These are typical calculations.

- For logic high,  $V_{OUT} = V_{OH\_MAX} = V_{CC\_MAX} 0.7V$  $(V_{CC\_MAX} - V_{OH\_MAX}) = 0.7V$
- For logic low, V<sub>OUT</sub> = V<sub>OL\_MAX</sub> = V<sub>CC\_MAX</sub> 1.5V
   (V<sub>CC\_MAX</sub> V<sub>OL\_MAX</sub>) = 1.5V

Pd\_H is power dissipation when the output drives high.

Pd\_L is the power dissipation when the output drives low.

$$Pd_{-}H = [(V_{OH\_MAX} - (V_{CC\_MAX} - 2V))/R_{L}] * (V_{CC\_MAX} - V_{OH\_MAX}) = [(2V - (V_{CC\_MAX} - V_{OH\_MAX}))/R_{L}] * (V_{CC\_MAX} - V_{OH\_MAX}) = [(2V - 0.7V)/50\Omega] * 0.7V = 18.2mW$$

$$Pd_{L} = [(V_{OL\_MAX} - (V_{CC\_MAX} - 2V))/R_{L}] * (V_{CC\_MAX} - V_{OL\_MAX}) = [(2V - (V_{CC\_MAX} - V_{OL\_MAX}))/R_{L}] * (V_{CC\_MAX} - V_{OL\_MAX}) = [(2V - 1.5V)/50\Omega] * 1.5V = 15mW$$

Total Power Dissipation per output pair = Pd\_H + Pd\_L = **33.2mW** 



#### **Case Temperature Considerations**

This device supports applications in a natural convection environment which does not have any thermal conductivity through ambient air. The printed circuit board (PCB) is typically in a sealed enclosure without any natural or forced air flow and is kept at or below a specific temperature. The device package design incorporates an exposed pad (ePad) with enhanced thermal parameters which is soldered to the PCB where most of the heat escapes from the bottom exposed pad. For this type of application, it is recommended to use the junction-to-board thermal characterization parameter  $\Psi_{JB}$  (Psi-JB) to calculate the junction temperature (T<sub>J</sub>) and ensure it does not exceed the maximum allowed junction temperature in the Absolute Maximum Rating table.

The junction-to-board thermal characterization parameter,  $\Psi_{JB}$ , is calculated using the following equation:

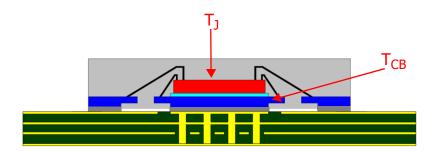
#### $T_J = T_{CB} + \Psi_{JB} \times P_d$ , Where

 $T_{.I}$  = Junction temperature at steady state condition in ( ${}^{\circ}$ C).

**T<sub>CB</sub> =** Case temperature (Bottom) at steady state condition in (°C).

 $\Psi_{JB}$  = Thermal characterization parameter to report the difference between junction temperature and the temperature of the board measured at the top surface of the board.

**P**<sub>d</sub> = power dissipation (W) in desired operating configuration.



The ePad provides a low thermal resistance path for heat transfer to the PCB and represents the key pathway to transfer heat away from the IC to the PCB. It's critical that the connection of the exposed pad to the PCB is properly constructed to maintain the desired IC case temperature  $(T_{CB})$ . A good connection ensures that temperature at the exposed pad  $(T_{CB})$  and the board temperature  $(T_{B})$  are relatively the same. An improper connection can lead to increased junction temperature, increased power consumption and decreased electrical performance. In addition, there could be long-term reliability issues and increased failure rate.

Example Calculation for Junction Temperature (T<sub>J</sub>): T<sub>J</sub> = T<sub>CB</sub> +  $\Psi$ <sub>JB</sub> x P<sub>d</sub>

Package type:	16-Lead VFQFPN
Body size:	3mm x 3mm x0.9mm
ePad size:	1.7mm x 1.7mm
Thermal Via:	2 x 2 matrix
$\Psi_{JB}$	5.1 C/W
T <sub>CB</sub>	105°C
P <sub>d</sub>	0.351 W

For the variables above, the junction temperature is equal to 107°C. Since this is below the maximum junction temperature of 125°C, there are no long term reliability concerns. In addition, since the junction temperature at which the device was characterized using forced convection is 111.2°C, this device can function without the degradation of the specified AC or DC parameters.



### **Reliability Information**

Table 9.  $\theta_{JA}$  vs. Air Flow Table for a 16-Lead VFQFPN

θ <sub>JA</sub> at 0 Air Flow					
Meters per Second	0	1	2.5		
Multi-Layer PCB, JEDEC Standard Test Boards	74.7°C/W	65.3°C/W	58.5°C/W		

#### **Transistor Count**

The transistor count for the 8SLVP1204 is: 258

# **Package Outline Drawings**

The package outline drawings are located at the end of this document and are accessible from the Renesas website (see Ordering Information for POD links). The package information is the most current data available and is subject to change without revision of this document.

### **Ordering Information**

**Table 10. Ordering Information** 

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
8SLVP1204ANLGI	204AI		Tube	-40°C to +85°C
8SLVP1204ANLGI8	204AI	3.0 × 3.0 × 0.9 mm 16-VFQFPN	Tape & Reel, Pin 1 Orientation: EIA-481-C	-40°C to +85°C
8SLVP1204ANLGI/W	204AI		Tape & Reel, Pin 1 Orientation: EIA-481-D	-40°C to +85°C

Table 11. Pin 1 Orientation in Tape and Reel Packaging

Part Number Suffix	Pin 1 Orientation	Illustration
8	Quadrant 1 (EIA-481-C)	CARRIER TAPE TOPSOE (Round Sprocket holes)  USER DIRECTION OF FEED
/W	Quadrant 2 (EIA-481-D)	CARRIER TAPE TOPSIDE (Round Sprocker Holes)  USER DIRECTION OF FEED

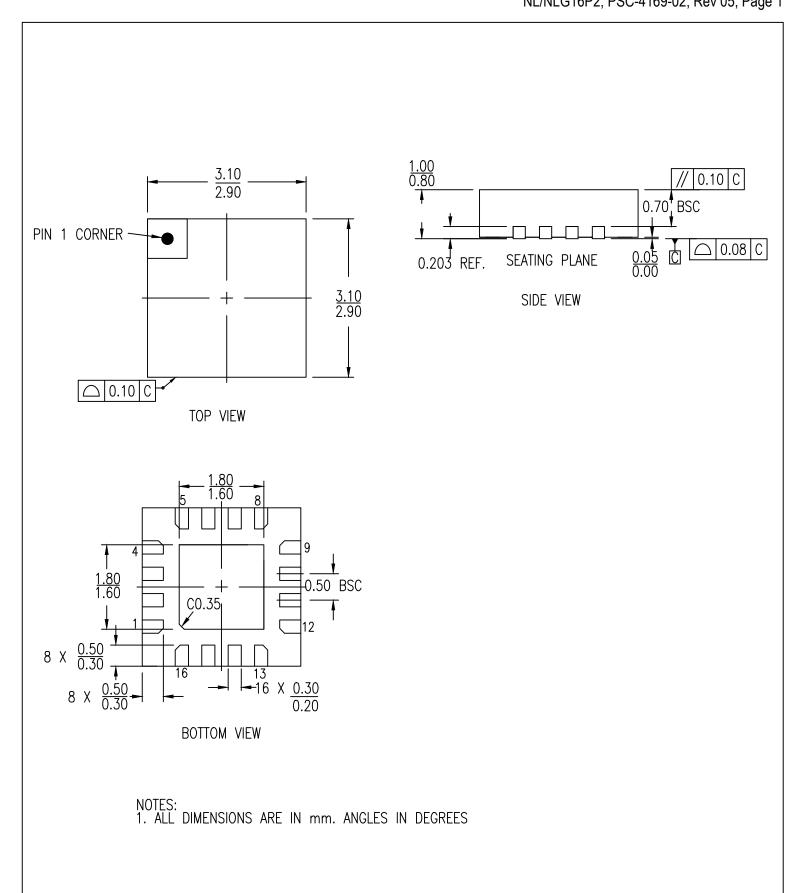


# **Revision History**

Revision Date	Description of Change		
May 20, 2021	<ul> <li>Added Termination for Q, nQ LVPECL Outputs AC-Coupled into HCSL-Receiver section.</li> <li>Added Features bullet: Supports PCI Express Gen1–5.</li> </ul>		
November 29, 2018	<ul> <li>Updated the description of Absolute Maximum Ratings.</li> <li>Added Recommended Operating Conditions.</li> </ul>		
September 13, 2018	Added Note 2 to Table 5B.		
March 13, 2018	<ul><li> Updated the package outline drawings; however, no technical changes.</li><li> Completed other minor changes.</li></ul>		
June 8, 2015	Features Section - Added Case Temperature bullet.      Added Case Temperature Considerations.		
December 19, 2014	AC Characteristic Tables - added V <sub>CMR</sub> spec.     Updated header/footer throughout the datasheet.		
February 25, 2014	Ordering Info: Changed Tray to Tube.		
March 20, 2014	$V_{PP}$ Deleted reference to NOTE 5; $V_{O}(pp)$ corrected typo ' $\leq$ '; $V_{DIFF\_OUT}$ corrected typo ' $\leq$ ' $V_{PP}$ Deleted reference to NOTE 5; $V_{O}(pp)$ corrected typo ' $\leq$ '; $V_{DIFF\_OUT}$ corrected typo ' $\leq$ ' Output Rise/Fall; changed $V_{SWING}$ to $V_{O}(pp)$		
January 27, 2014	ary 27, 2014 Changed NOTE 7 to read: V <sub>IL</sub> should not be less than -0.3V. V <sub>IH</sub> should not be higher than V <sub>CC</sub> .		
September 30, 2013	Features section, 10th bullet; changed 65mA to 60mA.  V <sub>REF</sub> ; added Minimum and Maximum values.  V <sub>OH</sub> ; added Minimum and Maximum values.  V <sub>OL</sub> ; added Minimum and Maximum values.		
April 8, 2013	<ul> <li>Features section - added Differential PCLK bullet referencing single-ended LVCMOS input.</li> <li>Added 3.3V ±10% Power Supply DC Characteristics Table.</li> <li>Added 3.3V ±10% LVCMOS/LVTTL DC Characteristics Table.</li> <li>Added 3.3V ±10% LVPECL DC Characteristics Table.</li> <li>AC Characteristics Table, added NOTE 6.</li> <li>Added 3.3V ±10% AC Characteristics Table and added NOTE 6.</li> <li>Parameter Measurement Information section - added 3.3V±10% LVPECL Output Load Test Circuit Diagram.</li> <li>Updated application note, Wiring the Differential Inputs to Accept Single-ended Levels.</li> <li>Updated Power Considerations section.</li> </ul>		



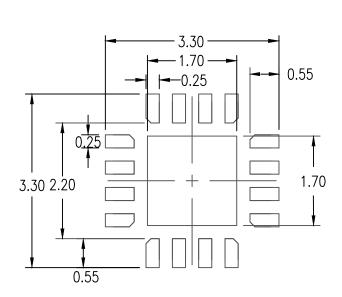
### 16-VFQFPN Package Outline Drawing 3.0 x 3.0 x 0.9 mm, 0.5mm Pitch, 1.70 x 1.70 mm Epad NL/NLG16P2, PSC-4169-02, Rev 05, Page 1





# 16-VFQFPN Package Outline Drawing

3.0 x 3.0 x 0.9 mm, 0.5mm Pitch, 1.70 x 1.70 mm Epad NL/NLG16P2, PSC-4169-02, Rev 05, Page 2



RECOMMENDED LAND PATTERN DIMENSION

#### NOTES:

- 1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES
- 2. TOP DOWN VIEW-AS VIEWED ON PCB
- 3. LAND PATTERN RECOMMENDATION IS PER IPC-7351B GENERIC REQUIREMENT FOR SURFACE MOUNT DESIGN AND LAND PATTERN

Package Revision History					
Date Created	Rev No.	Description			
Oct 25, 2017	Rev 04	Remove Bookmak at Pdf Format & Update Thickness Tolerance			
Jan 18, 2018	Rev 05	Change QFN to VFQFPN			

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